

**Amendments to the Specification:**

Please replace the title with:

**SHIELDED MAGNETIC RAM CELLS**

Page 4, line 16

To more particularly illustrate the method and system in accordance with the present invention, refer now to Figure 21 depicting one embodiment of a magnetic memory 100 in accordance with the present invention. The magnetic memory 100 is formed on a semiconductor substrate 102, which preferably includes semiconductor devices, such as integrated circuits. The magnetic memory 100 includes magnetic tunneling junctions 110. Each magnetic tunneling junction 110 includes two ferromagnetic layers 112 and 116 with an insulating layer 114 between the ferromagnetic layers 112 and 116. Charge carriers are capable of tunneling between the ferromagnetic layers 112 and 116. Note that the magnetic tunneling junctions 110 may include other components, such as an antiferromagnetic layer used to pin the magnetization of one of the ferromagnetic layers 112 and 116. The magnetic tunneling junctions 110 are separated by insulator. In addition, an insulating layer 120 is provided on the magnetic tunneling junctions 112.